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APPLICATION FOR LETTERS PATENT

**Monitoring In-Use Memory Areas for Power  
Conservation**

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1 **TECHNICAL FIELD**

2 This invention relates to memory devices and systems and power  
3 conservation in such devices and systems.  
4

5 **BACKGROUND**

6 Dynamically refreshed memory, usually referred to as dynamic random  
7 access memory or DRAM, is a type of memory device found in many different  
8 computing devices. A typical DRAM device may have millions, billions or even  
9 more DRAM memory cells. A DRAM memory cell is commonly formed by a  
10 single transistor and an associated capacitance. The capacitance is charged to a  
11 voltage that indicates a bit value of either "0" or "1". The capacitance loses its  
12 charge rather quickly, bringing about the need for periodic refreshing.

13 In many computer systems, the power consumption of DRAM memory is  
14 insignificant compared to other system components such as hard disks, high-  
15 performance microprocessors, active matrix displays, CRTs, etc. However, in  
16 other computer systems, such as the newly emerging and evolving class of mobile  
17 devices known as "handhelds" or "PDAs" ("personal digital assistants"), the  
18 power consumption of the DRAM memory is significant as compared to other  
19 components in the computer system. In comparison to many of the more  
20 traditional types of computers, such as desktop or personal computers, many  
21 mobile computing devices, are smaller, less capable, and use components that  
22 consume less power. For example, many of these systems have small,  
23 monochromatic displays, low performance CPUs, and no hard disks. Some of these  
24 mobile systems, furthermore, rely on batteries for their operating power. As a  
25 result of these factors, power consumption of memory subsystems has become

more of an issue in these devices; there is a strong need to reduce memory power consumption and to thereby extend the time between required battery replacement or recharging.

Memory devices with power management features are becoming available to address this need. For example, DRAMs are available that support various different reduced power modes. However, power savings come at the cost of performance. Typically, a greater penalty in access speed is imposed at each increasing degree of power savings.

#### **BRIEF DESCRIPTION OF THE DRAWINGS**

Fig. 1 is a block diagram of a memory system that incorporates aspects of the present invention.

Fig. 2 is a block diagram showing pertinent parts of a memory controller and memory device of the present invention.

Fig. 3 is a flowchart showing actions performed to refresh a memory row in accordance with the present invention.

Figs. 4-6 are block diagrams showing pertinent parts of a memory controller and memory device in alternative embodiments of the present invention.

Fig. 7 is a flowchart showing actions performed in the embodiment of Fig. 6 to refresh a memory row in accordance with the present invention.

Fig. 8 is a block diagram showing pertinent parts of a memory controller and memory device in another embodiment of the present invention.

## DETAILED DESCRIPTION

Fig. 1 shows pertinent portions of a computer system 10, including a CPU 12, a memory controller 14, and memory devices 16. Although the memory controller and memory devices are shown to be separate entities in this figure, the same techniques apply for memory controllers that are integrated into the CPU, as well as memory that is integrated with either the controller and/or the CPU.

The computer system also includes an operating system 18 and one or more applications or application programs 20. The operating system and applications are typically initially stored on some form of non-volatile memory (not shown). They are subsequently loaded into executable memory and executed by CPU 12. Devices 16 form at least part of the executable memory. In many cases, the computer system implements a virtual memory system, so that only portions of the operating system and applications are actually present in physical memory at any given time.

The architecture of Fig. 1 is typical of many computers and computer-like devices, and is not limited to conventional desktop systems or even to conventional portable computer systems. Many types of devices, such as entertainment and game devices, industrial control devices, and others either use an architecture such as this or can be easily adapted to use such an architecture.

The operating system is typically an off-the-shelf, general-purpose operating system that provides low-level management functions and support for higher-level application programs. However, the operating system might alternatively be a custom application or program designed for a particular, specialized purpose, and might itself perform the specialized functions that would in other cases be performed by separate application programs.

1 In the described embodiment, memory devices 16 have dynamically  
2 refreshable memory cells. Such devices are typically referred to as DRAMs  
3 (dynamic random access memory), or DRAM devices. Other types of memory  
4 devices can, however, also benefit from the techniques described herein.

5 Memory controller 14 acts as an interface between CPU 12 and the memory  
6 devices. Memory controller 14 has refresh logic 21 that is configured to  
7 periodically refresh the memory cells of the memory devices.

8 Fig. 2 shows memory controller 14 and one of memory devices 16 in more  
9 detail. Each of memory devices 16 has multiple dynamically refreshable memory  
10 cells, arranged in rows 22. In operation, memory controller 14 can receive  
11 memory instructions from various sources, including but not limited to, operating  
12 system 18, CPU 12, a graphics adapter (not shown), and/or other sources.  
13 Memory controller 14 responds to the instructions by performing various memory  
14 operations such as, for example, reads and writes.

15 Although not shown, memory device 16 also has a plurality of sense  
16 amplifiers. The sense amplifiers are typically arranged in one or more rows. In  
17 many systems, one row of sense amplifiers is associated with a plurality, or bank,  
18 or memory cells. A read operation typically involves reading an entire row of  
19 memory cells into an associated row of sense amplifiers. This initial operation is  
20 sometimes referred to as a "Row Address Strobe", or "RAS", operation, although  
21 more accurately it is referred to as a "sense" or "activate" operation. It is also  
22 possible for the "sense" operation to read less than, or even more than, one entire  
23 row of bits to the plurality of sense amplifiers. Following the "sense" operation,  
24 one or more of the sense amplifiers are read by memory controller 14.

1 The RAS or "sense" operation is destructive—the transfer of data from the  
2 memory cells to the sense amplifiers destroys the data held by the memory cells.  
3 Accordingly, data in the sense amplifiers are written back to the memory cells  
4 after the sense operation.

5 A write operation is similar, in that row data is initially read to the sense  
6 amplifiers in a sense operation. After the initial sense operation, an operation  
7 sometimes referred to as a "Column Address strobe" or "CAS" operation is  
8 performed to write new data to at least some of the sense amplifiers and to the  
9 corresponding memory cells.

10 In order to ensure that data in each of the memory cells remains accurate,  
11 the data in the memory cells is periodically refreshed in a refresh operation. A  
12 refresh operation typically comprises reading a row to the sense amplifiers and  
13 then writing the same data back to the row. Memory controller 14 is typically  
14 configured to perform periodic refresh cycles on its own, without receiving  
15 instructions from the CPU; generally, the CPU is unaware of refresh cycles. In  
16 many prior art systems, a refresh operation is performed on every memory cell in  
17 every memory row of a memory device at least once during each refresh period.  
18 The refresh period has a duration equal to a parameter often referred to as  
19 "TREF", and the refresh period is often referred to as the TREF period.

20 The embodiments described herein include circuits and logic for keeping  
21 track of which memory cells or memory areas are actually in use. When the  
22 memory is dynamically refreshable memory such as DRAM, a reduction in power  
23 consumption can be implemented by omitting or skipping refreshing of unused  
24 cells or areas. An added benefit is that refresh operations can be limited to only  
25 those memory cells that are storing useful data. By reducing the number of

1 useless refresh operations being performed (which can delay subsequent requests  
2 from requestors such as the CPU), the memory system is more available for  
3 memory requests, increasing performance by reducing latency and increasing  
4 bandwidth. Thus, the present embodiment includes circuits and logic for keeping  
5 track of which memory rows are actually in use and therefore need refreshing.  
6 Disclosed embodiments also include circuits and logic for periodically refreshing  
7 those memory rows that are in use, and for omitting refreshing of memory rows  
8 that are not in use. Omitting refreshing of identified, non-used areas of memory  
9 can provide significant power savings as well as increases in performance.

10 More specifically, the described embodiments include one or more  
11 dynamically changeable use registers 24. Such use registers are shown in Fig. 1 as  
12 being implemented apart from either the memory controller or the memory  
13 devices. In preferred embodiments shown by Figs. 2 and 4, however, the use  
14 registers are implemented as part of the memory devices 16 or as part of memory  
15 controller 14.

16 In the embodiment of Fig. 2, each memory device includes one or more  
17 dynamically changeable use registers 24. These registers indicate used and unused  
18 memory cells or groups of memory cells. More specifically, use registers 24 in  
19 this embodiment comprise individual bits or flags that are associated respectively  
20 with individual memory cell rows. Each bit or flag is set to indicate whether the  
21 corresponding row is actually in use, and whether it therefore needs to be  
22 refreshed. The term "in use" means merely that the data stored by the "in use"  
23 memory is intended to remain valid and non-volatile. The determination of  
24 whether a memory area is "in use" is made by memory controller 14, CPU 12,  
25 operating system 18, or applications 20, as will be described in more detail below.





1 application program requesting the use of additional memory during actual  
2 execution of the application program. In response to requests such as this, the  
3 operating system designates areas of physical memory for exclusive use by the  
4 requesting application programs.

5 In accordance with this embodiment of the invention, the operating system  
6 is configured to notify memory controller 14 in response to memory allocations  
7 such as those described above. In addition, the operating system is configured to  
8 notify memory controller 14 in response to memory de-allocations. Allocated  
9 memory is deemed to be in-use, and de-allocated memory (or any memory that has  
10 not yet been allocated) is deemed not to be in-use.

11 Memory devices 16 are often referred to collectively as "physical" or  
12 "primary" memory. Physical memory is characterized by being randomly  
13 accessible through the specification of physical memory addresses: CPU 12  
14 accesses memory devices 16 by specifying physical memory addresses to memory  
15 controller 14. The available range physical memory addresses is often referred to  
16 as a physical address space. Because the amount of physical memory is finite, the  
17 physical address space is also finite and in some cases is relatively small compared  
18 to the needs of operating system 18 and application programs 20.

19 In order to provide a larger effective address space, many operating systems  
20 implement "virtual" memory. In a virtual memory system, each application  
21 program has available its own relatively large virtual address space. Each such  
22 virtual address space is typically larger than the physical address space.

23 In systems such as this, the operating system typically allocates virtual  
24 memory to requesting application programs. When such virtual memory is  
25 allocated, the operating system creates a translation entry or "mapping" between

an allocated range of virtual memory addresses and a corresponding range of physical memory addresses. Each translation entry or mapping translates from a virtual or source address to a physical or target address. The operating system maintains a translation or mapping table that contains all current translations or mappings.

When an application program subsequently references a virtual memory address, the operating system and CPU use the translation table to translate from the virtual address to the physical address, and the actual memory access is made to the indicated physical address. This translation process is transparent to the application programs.

Each application program typically executes in its own virtual address space. To make each virtual address space appear relatively unlimited, the operating system makes use of a mass storage medium such as a hard disk, which is typically referred to as secondary storage or secondary memory to distinguish it from primary or physical memory. Secondary storage is usually relatively slow to access, but normally has a capacity much larger than that of primary memory. The operating system monitors memory usage and when portions of virtual memory are not being used, the data from the corresponding portions of physical memory is moved to secondary storage. Thus, at any given time, some portions of virtual memory will correspond to portions of physical memory, and some virtual memory will correspond to portions of secondary memory.

If an application program attempts to access a portion of virtual memory that is currently held in secondary storage, there will be no appropriate entry in the translation table. This is referred to as a "miss," in response to which the operating system intervenes, loads the appropriate data back into physical memory

1 and creates an appropriate translation entry in the translation table. After this is  
2 accomplished, the control is returned to the application program, which accesses  
3 the memory in its normal fashion.

4 The process of moving data between primary and secondary storage is  
5 referred to as memory "swapping" and normally takes place on an ongoing basis.  
6 As part of this process, the operating system maintains and updates its virtual-to-  
7 physical address mappings so that any reference to a virtual memory address will  
8 be translated to the appropriate physical address. The virtual-to-physical  
9 mappings change frequently in response to memory swapping.

10 Thus, in systems that support virtual memory, the operating system  
11 allocates *virtual* memory to requesting application programs. Prior to use,  
12 however, the operating system loads needed portions of the virtual memory into  
13 portions of physical memory, and provides address translations between virtual  
14 and physical memory addresses. In systems such as these, physical memory can  
15 be considered to be allocated whenever it is the target of an active virtual-to-  
16 physical memory mapping as described above. The operating system is  
17 configured to notify controller 14 when memory becomes allocated in this fashion.

18 Regardless of the method of physical memory allocation, the operating  
19 system is configured to identify allocated memory to memory controller 14 when  
20 physical memory is allocated for use. Similarly, the operating system is  
21 configured to instruct or notify memory controller 14 when physical memory is  
22 de-allocated and is no longer in use. Memory controller 14 responds by refreshing  
23 currently allocated memory, and by not refreshing memory that is not currently  
24 allocated. More specifically, either memory controller 14 or the memory device  
25 responds by setting or programming use registers 24, depending on whether the



1 use, the memory device performs the refresh operation 32. If the row is not in use,  
2 the memory device skips block 32 and omits the refresh operation.

3 This configuration also works well in conjunction with systems utilizing  
4 broadcast refreshes. In systems such as this, the memory controller can send  
5 broadcast refresh requests to the memory devices, and the memory devices can  
6 ignore such requests for any unused rows, as determined by the use registers  
7 located on the individual memory devices.

8 Although the use registers or flags 24 are shown on individual memory  
9 devices for purposes of this example, the registers or flags could be physically  
10 located elsewhere. For example, they could be located on the memory controller,  
11 or on some other component other than the memory controller or memory device.  
12 Fig. 4 shows an implementation in which use registers or flags 24 are located on  
13 memory controller 14. If the use registers are located on the memory controller,  
14 the memory controller itself preferably determines whether to refresh individual  
15 rows. Specifically, the memory controller sends instructions only for those rows  
16 that are indicated to be in use, and omits refresh instructions for rows that are not  
17 in use.

18 Fig. 5 shows another implementation. In this implementation, it is  
19 advantageous to locate the use registers on the memory devices. Each memory  
20 device in this implementation includes self-refresh logic 34. Such self-refresh  
21 logic is typically utilized in reduced power modes of DRAM memory devices. In  
22 normal operation, refreshes are performed by memory controller 14. In reduced  
23 power modes, refreshes are performed by the self-refresh logic of the memory  
24 devices themselves.

Before a device enters self-refresh mode, use bits can be set whenever a read or write operation is performed to a row of the memory device. They can be cleared by explicit commands to the memory device, originated by the memory controller, operating system, or application, for example.

When a DRAM enters self-refresh, these bits can be checked to determine if a row needs to be refreshed or not. Specifically, self-refresh logic 34 is responsive to the use registers or flags 24 to determine whether to refresh individual rows. Self-refresh logic 34 refreshes a row if the corresponding use register indicates that the row is in use, and omits refreshing for any particular row if that row's use register indicates that the row is unused.

Although the use registers have been described and shown as corresponding to respective rows, they could alternatively correspond to sets of memory cells defined in some other way. For example, each use register or flag might correspond to a group of memory cells, a bank of memory cells, or a page of memory cells. In this case, a single use flag indicates whether or not the memory cells of a memory bank or page are in use. The flag is set to a true value if any cells of the bank or page are being used. During refreshing, all rows or cells of the bank or page are refreshed when the corresponding use register indicates that the bank or page is in use.

Fig. 6 shows yet another implementation. This implementation is similar to that of Fig. 2, in that use registers 24 are located on memory device 16. In addition, however, this implementation includes a plurality of "recent-access" registers or flags 36. Each such recent-access register 36 corresponds to a row of memory cells, and indicates whether the associated memory row was accessed, during the previous refresh cycle interval, in a manner that had the effect of

1 refreshing the cells of the memory row. For example, in many types of DRAMs, a  
2 RAS or "activate" operation, although not explicitly comprising a refresh  
3 operation, has the same side-effects as a refresh operation with respect to the row  
4 upon which the RAS operation acts. Specifically, some types of memory  
5 operations other than explicit refresh operations have the effect of refreshing  
6 memory cells. In these types of DRAMs, if a RAS or activate operation is  
7 performed on a row, this can be tracked by the recent-access register  
8 corresponding to that row, indicating that a refresh operation is not needed for that  
9 row during the current interval.

10 Thus, each time a memory row is accessed in a manner that has the effect  
11 of a refresh operation (but is not an explicit refresh operation), that row's recent-  
12 access register is set—either by memory controller 14 or by memory device 16.  
13 This indicates that the row has been refreshed during the previous refresh period  
14 by some operation other than an explicit refresh operation. This allows refreshing  
15 of recently accessed memory rows to be omitted.

16 Fig. 7 shows refreshing actions performed by memory controller 14 with  
17 respect to each row of a memory device in accordance with the implementation  
18 shown by Fig. 6. These actions are initiated at least once for every memory row  
19 during every refresh period TREF. Prior to refreshing a row, as illustrated by  
20 block 40, memory controller 14 accesses the appropriate use register 24 to  
21 determine whether the row is in use. If the row is not in use, the subsequent  
22 refreshing operation 42 is skipped. If the row is in use, an operation 44 accesses  
23 the appropriate recent-access register 36 to determine whether the current row has  
24 already been refreshed during the previous refresh cycle interval. If the row has  
25 already been refreshed, refreshing operation 42 is skipped. Refreshing 42 is

1 performed only if use register 24 is true and recent-access register 36 is false. As  
2 a concluding operation 46, recent-access register 36 is reset for the next refresh  
3 period.

4 Although the described implementation includes the recent-access registers  
5 as part of individual memory devices, they might alternatively be implemented  
6 elsewhere, such as on a memory controller. Furthermore, each recent-access  
7 register or flag might correspond to a set of memory cells other than a row, such as  
8 a group of memory cells, a bank of memory cells, or a page of memory cells.

9 An alternative embodiment might include the concept of recent-access  
10 registers, apart from use registers. In an embodiment such as this, the memory  
11 controller or memory device checks only whether a particular row has been  
12 recently refreshed before proceeding with the refresh operation. Although this  
13 embodiment allows refreshing of memory areas that may not be in actual use, it  
14 relieves the operation system of the burden of notifying the memory components  
15 about such memory usage.

16 Fig. 8 shows yet another implementation. This implementation is similar to  
17 that shown in Fig. 2, and the same reference numerals have therefore been used for  
18 similar or identical components. In this implementation, however, memory  
19 controller 14 includes a cache or buffer 50 that is used to cache individual memory  
20 rows of memory device 16. Specifically, memory controller 14 is configured to  
21 buffer or cache at least some of those memory rows whose use registers indicate  
22 they are in use. The refresh logic of memory controller 14 is configured to then  
23 operate the cached memory device rows in reduced power modes, such as by  
24 omitting refreshing for those rows that have been cached.



1 To omit refreshing for cached rows, the memory controller programs the  
2 use registers of the rows to indicate that the rows are no longer in use. Once a  
3 memory row is cached, subsequent accesses to cached memory are made directly  
4 to and from cache 50, instead of from the memory devices 16. When the memory  
5 row is no longer cached, and its contents are flushed back to the corresponding  
6 memory row, the corresponding use flag is reprogrammed to indicate that the row  
7 is again in use.

8 Although the techniques above have been described in relation to DRAM  
9 memory in which power saving are accomplished by omitting the refreshing rows  
10 of unused memory areas, the concept of tracking in-use memory areas can  
11 potentially be applied to other types of memory devices to reduce power  
12 consumption. For example, certain types of memory devices might have built-in  
13 reduced power modes, in which less power is consumed at the expense of greater  
14 access latency. By identifying unused portions of memory, it is possible to invoke  
15 such reduced power modes in an intelligent manner to lessen any detrimental  
16 effects of the reduced power modes. Specifically, it is possible to invoke such  
17 reduced power modes only for devices or portions of devices in which either no  
18 memory is currently in use or relatively little memory is in use.

19 Similarly, the caching concept introduced with reference to Fig. 8 can be  
20 used advantageously with memory devices having built-in reduced power modes.  
21 To take advantage of such reduced power modes, the memory controller first  
22 identifies targeted areas of memory based on usage. In conjunction with the  
23 techniques discussed above, the memory controller can identify these areas of  
24 memory based on whether their use flags are set. In other embodiments, the  
25

1 memory controller might monitor memory usage and identify areas of memory  
2 that are accessed most frequently.

3 After identifying targeted areas of memory that are in use or that are  
4 currently receiving high usage, the controller is configured to cache such areas in  
5 cache 50. The controller then identifies the memory devices containing the  
6 targeted memory or significant portions of the targeted memory, and sets those  
7 memory devices to reduced power modes.

8 In one embodiment, cache 50 is preferably large enough to cache the entire  
9 memory contents of one or more memory devices. In this embodiment, the  
10 memory controller identifies the memory device receiving the highest usage, and  
11 caches the entire contents of the identified memory device.

12 However, this technique is also applicable in systems where cache 50 is  
13 smaller. In systems where cache 50 is too small to cache an entire memory  
14 device, at least the most frequently accessed memory portions of the device are  
15 cached. Remaining portions are accessed in the reduced power mode at  
16 potentially slower access speeds. Because these remaining portions are less  
17 frequently used, however, the slower speeds will have minimal effect.

18 The techniques described above can be used in many systems to produce  
19 significant power savings. Furthermore, such power savings will often have few  
20 or no detrimental side-effects, because the power-saving measures are taken with  
21 respect to memory areas that are not actually being used. The described  
22 techniques therefore avoid the prior art tradeoff between access speed and power  
23 savings.

24 Although details of specific implementations and embodiments are  
25 described above, such details are intended to satisfy statutory disclosure

obligations rather than to limit the scope of the following claims. Thus, the invention as defined by the claims is not limited to the specific features described above. Rather, the invention is claimed in any of its forms or modifications that fall within the proper scope of the appended claims, appropriately interpreted in accordance with the doctrine of equivalents.

TOO LONG TO REPEAT